

MC1545GRS LDMOS TRANSISTOR

Document Number: MC1545GRS
Product Datasheet V1.0

450W, P band High Power RF LDMOS FETs

MC1545GRS

Description

The MC1545GRS is a 450-watt, unmatched, high ruggedness, single ended LDMOS FETs, designed for P band application up to 0.7GHz.

It can be used in Class AB/B and Class C for any pulse and CW signal.

- Typical 500M narrow band RF Performance (On Innogration fixture with device soldered):

$V_{DS} = 28V$, $I_{DQ} = 10mA$, $V_{GS} = 2.66V$



Signal	P1dB (dBm)	P1dB (W)	P1dB Eff (%)	P1dB Gain (dB)	P3dB (dBm)	P3dB (W)	P3dB Eff (%)
Pulse	55.54	358	69.37	21.31	56.51	450	73

Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

Suitable Applications

- P band pulse or CW amplifier
- ISM applications

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DS}	+65	Vdc
Gate--Source Voltage	V_{GS}	-10 to +10	Vdc
Operating Voltage	V_{DD}	+30	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	+150	°C
Operating Junction Temperature	T_J	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case $T_C = 85^{\circ}C$, $T_J = 200^{\circ}C$, DC test	$R_{\theta JC}$	0.17	°C/W

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22--A114)	Class 2

Table 4. Electrical Characteristics ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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DC Characteristics

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65V$, $V_{GS} = 0V$)	I_{DSS}			100	μA
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28V$, $V_{GS} = 0V$)	I_{DSS}			1	μA
Gate--Source Leakage Current	I_{GSS}			1	μA

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(V _{GS} = 10 V, V _{DS} = 0 V)					
Gate Threshold Voltage (V _{DS} = 28V, I _D = 450 μA)	V _{GS(th)}		1.9		V
Gate Quiescent Voltage (V _{DD} = 28 V, I _D = 1A, Measured in Functional Test)	V _{GS(Q)}		2.66		V

Load Mismatch (In Innogration Test Fixture, 50 ohm system): V_{DD} = 28 Vdc, I_{DQ} = 10 mA, f = 700 MHz

VSWR 10:1 at 450W pulse CW Output Power	No Device Degradation
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TYPICAL CHARACTERISTICS

Figure 1. Network analyzer output S11/S21 (VDS=28V IDQ=1000mA)

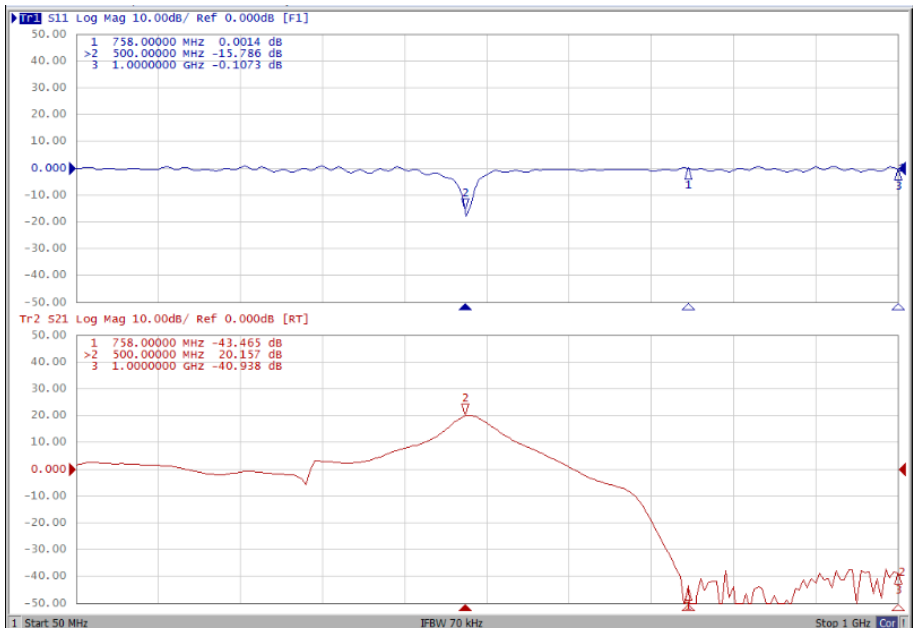
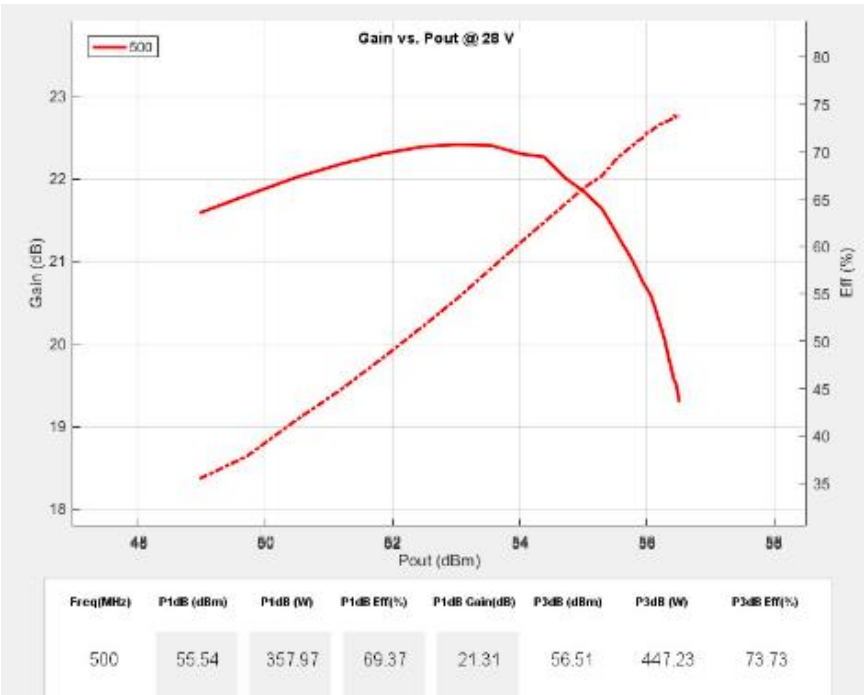


Figure 2. Gain, Efficiency as function of Pout



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Figure 3. Test Circuit Component Layout

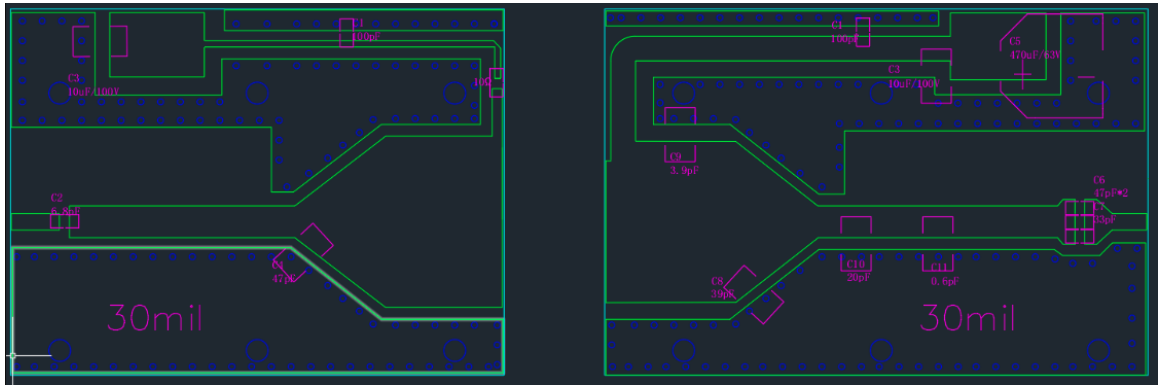


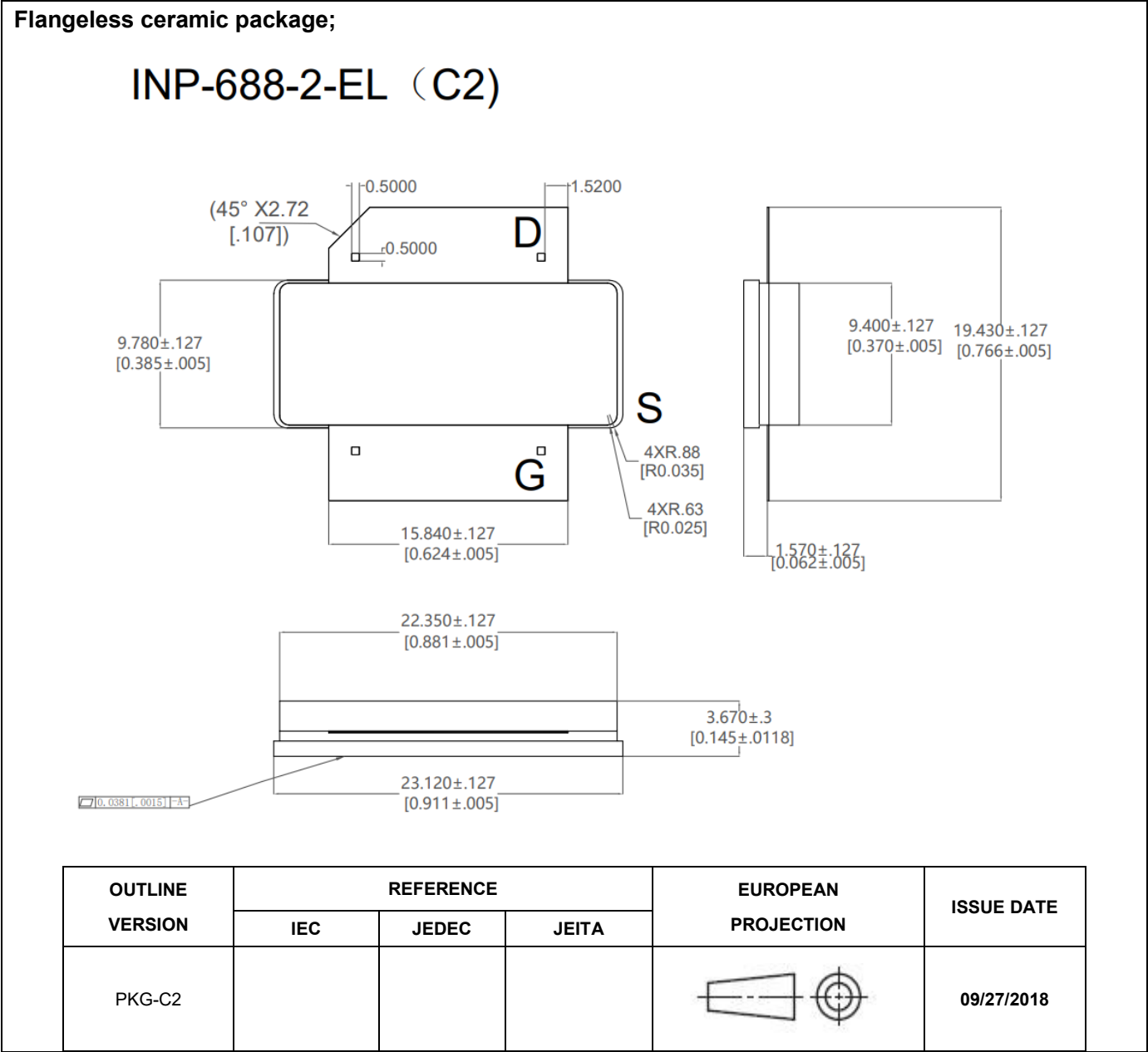
Table 5. Test Circuit Component Designations and Values

Component	Value	Quantity
C1	100pF	2
C3	10uF	2
R1	10 ohm	1
C2	6.8pF	1
C5	470uF	1
C4	47pF	1
C6	47pF	2
C7	33pF	1
C8	39 pF	1
C9	3.9 pF	1
C10	20 pF	1
C11	0.6 pF	1
C16、C17	1nF	2
R1	50Ω	1
R2、R3、R4	10 Ω	3
C21	470uF/63V	1

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Package Outline



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Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2024/5/31	Rev 1.0	Product Datasheet

Application data based on ZXY-24-15

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